

650V N-Channel Super Junction MOSFET

Voltage	650 V	Rdson	210 mΩ
Current	19 A	Qg	34 nC

Feature:

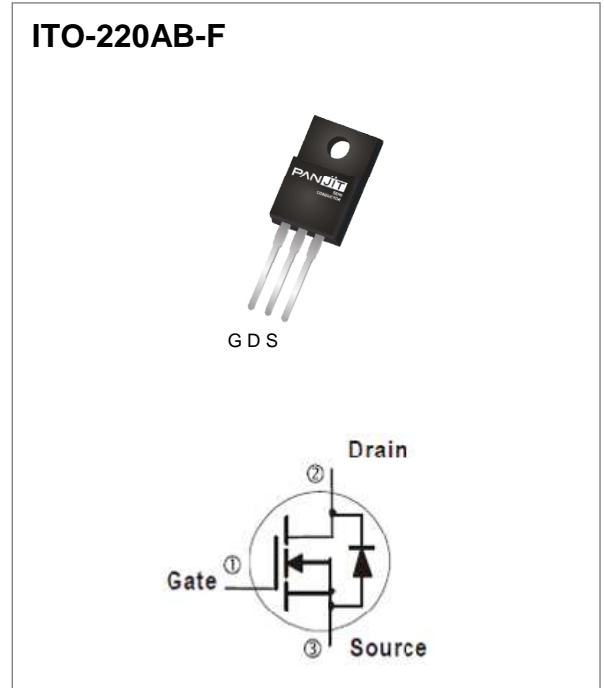
- $R_{DS(ON) Max}$, $V_{GS@10V}$: 210mΩ
- Easy to use/ drive
- High Speed Switching and Low $R_{DS(ON)}$
- 100% Avalanche Tested
- 100% Rg Tested
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case: ITO-220AB-F package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 2 grams

Application

- PFC, TV Power, PC Power, PD Charger, Adapter, UPS



Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise specified)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage @ T_{jmax}		V_{DS}	700	V
Drain-Source Voltage		V_{DS}	650	
Gate-Source Voltage		V_{GS}	± 30	
Continuous Drain Current	$T_C=25^\circ\text{C}$	I_D	19.0	A
	$T_C=100^\circ\text{C}$		11.2	
Pulsed Drain Current	$T_C=25^\circ\text{C}$	I_{DM}	42	A
Single Pulse Avalanche Energy		E_{AS}	420	mJ
MOSFET dv/dt ruggedness		dv/dt	50	V/ns
Power Dissipation	$T_C=25^\circ\text{C}$	P_D	32	W
	$T_C=100^\circ\text{C}$		12.8	
Insulation Withstand Voltage for ITO-220AB-F		V_{ISO}	3.5	kV
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	$^\circ\text{C}$

Thermal Characteristics

PARAMETER		SYMBOL	MAXIMUM	UNITS
Thermal Resistance	Junction-to-Case	$R_{\theta JC}$	3.9	$^\circ\text{C/W}$
	Junction-to-Ambient (Note 3)	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$

Electrical Characteristics ($T_A = 25\text{ }^\circ\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	650	730	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2	3.0	4	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=9.5A$ (Note 1)	-	183	210	m Ω
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=650V, V_{GS}=0V$	-	-	1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 30V, V_{DS}=0V$	-	-	± 100	nA
Transfer characteristics	gfs	$V_{DS}=20V, I_D=19A$	-	21.8	-	S
Dynamic (Note 5)						
Total Gate Charge	Q_g	$V_{DS}=520V, I_D=19A,$ $V_{GS}=10V$	-	34	-	nC
Gate-Source Charge	Q_{gs}		-	7.7	-	
Gate-Drain Charge	Q_{gd}		-	13.5	-	
Input Capacitance	C_{iss}	$V_{DS}=400V, V_{GS}=0V,$ $f=250kHz$	-	1412	-	pF
Output Capacitance	C_{oss}		-	50	-	
Reverse Transfer Capacitance	C_{rss}		-	6.8	-	
Effective Output Capacitance Energy Related	$C_{o(er)}$		$V_{DS}=0V$ to 400V, $V_{GS}=0V, f=250kHz$ (Note 4)	-	64	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=325V, I_D=19A,$ $V_{GS}=10V, R_G=25\Omega$ (Note 2)	-	30	-	ns
Turn-On Rise Time	t_r		-	65	-	
Turn-Off Delay Time	$t_{d(off)}$		-	111	-	
Turn-Off Fall Time	t_f		-	61	-	
Gate Resistance	R_g	$f=1.0MHz$	-	1.7	-	Ω
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I_S		-	-	19	A
Diode Forward Voltage	V_{SD}	$I_S=19A, V_{GS}=0V$	-	0.9	1.5	V
Reverse Recovery Charge	Q_{rr}	$I_S=19A$	-	5.7	-	μC
Reverse Recovery Time	T_{rr}	$di/dt=100A/\mu s$	-	370	-	ns

NOTES :

1. Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
2. Essentially independent of operating temperature typical characteristics.
3. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance.
4. $C_{o(er)}$ is a capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0V to 80% $V_{(BR)DSS}$
5. Guaranteed by design, not subject to production testing

TYPICAL CHARACTERISTIC CURVES

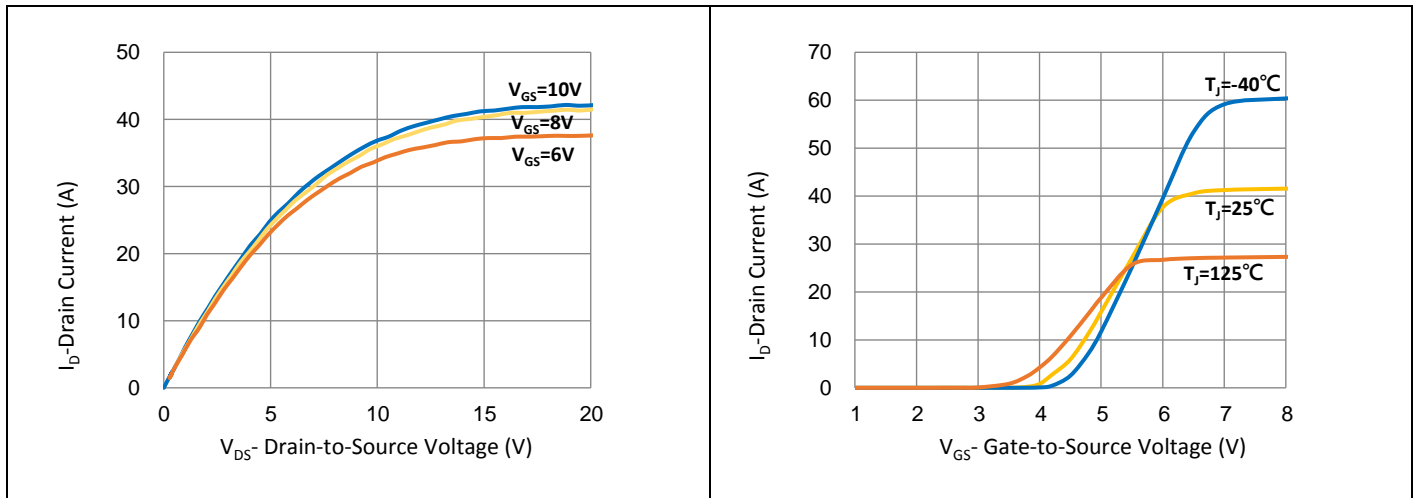


Fig.1 Output Characteristics

Fig.2 Transfer Characteristics

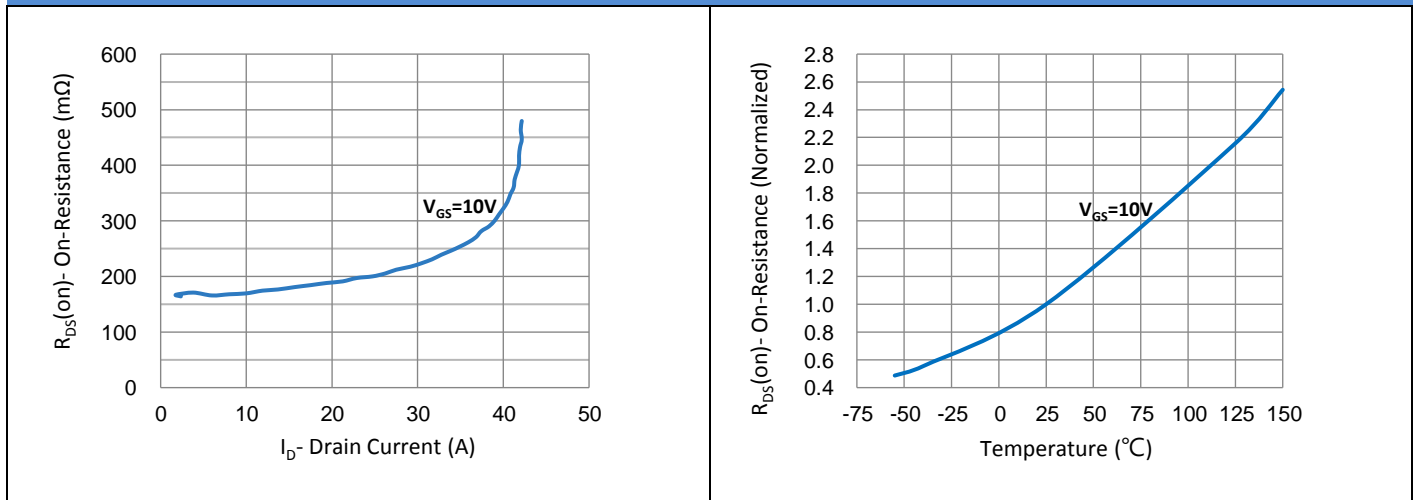


Fig.3 On-Resistance vs. Drain Current

Fig.4 On-Resistance vs. Junction Temperature

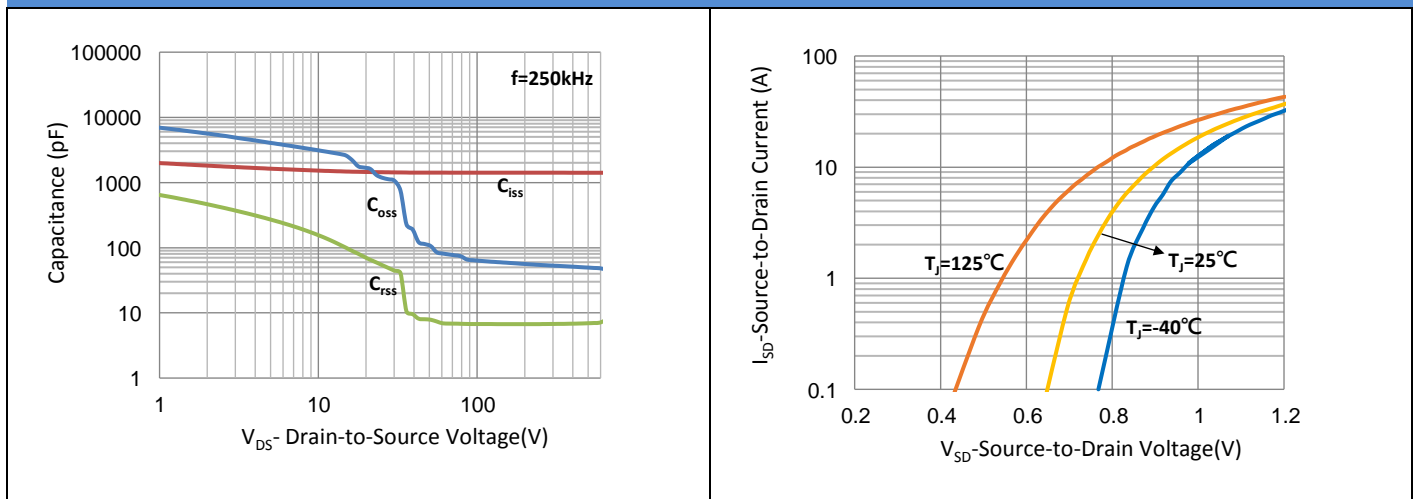


Fig.5 Capacitance vs. Drain-Source Voltage

Fig.6 Source-Drain Diode Forward Voltage

TYPICAL CHARACTERISTIC CURVES

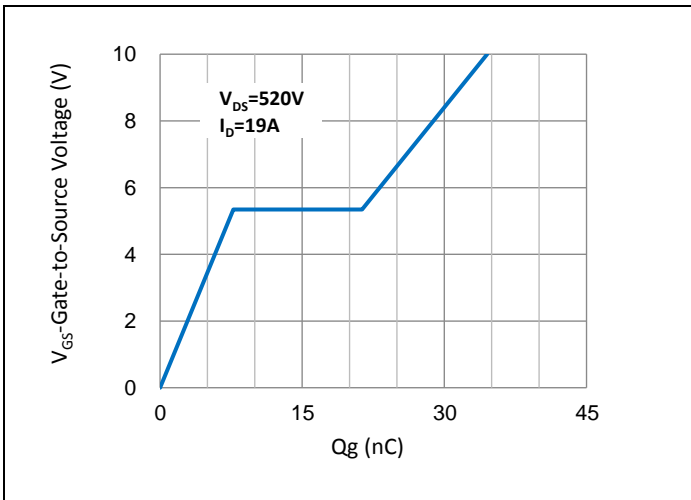


Fig.7 Gate-Charge Characteristics

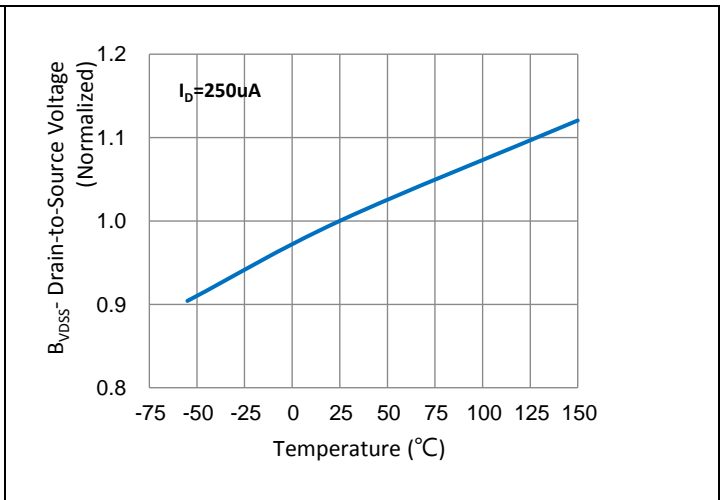


Fig.8 Breakdown Voltage Variation vs. Temperature

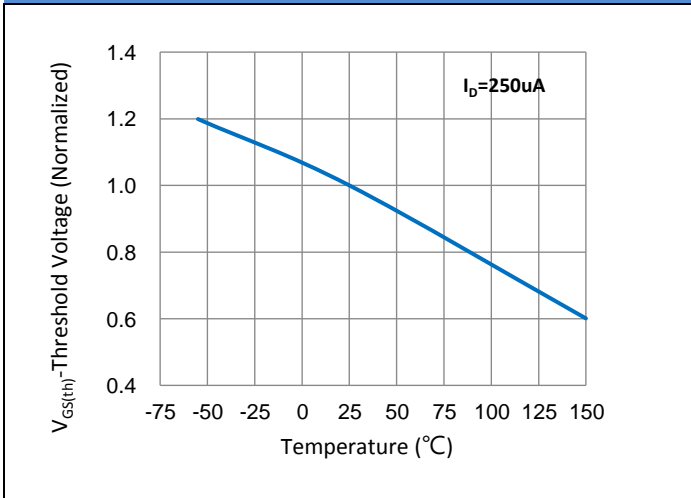


Fig.9 Threshold Voltage Variation with Temperature

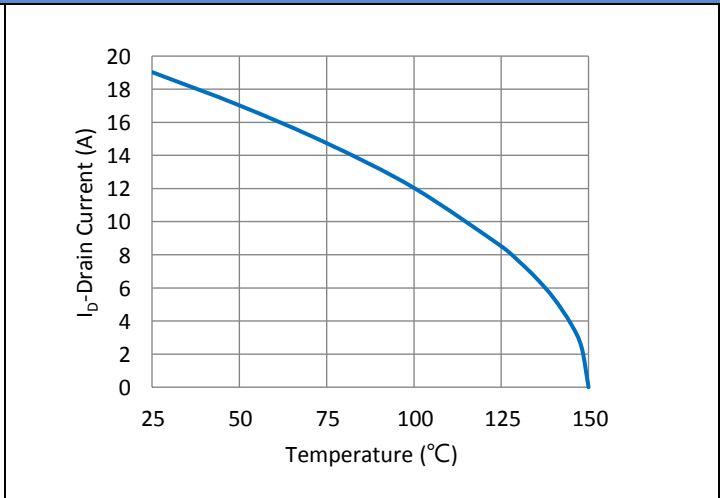


Fig.10 Drain Current vs. Case Temperature

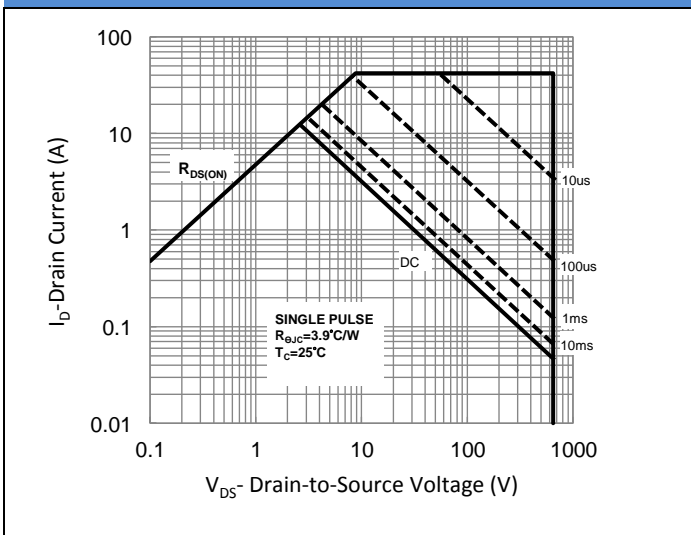


Fig.11 Maximum Safe Operating Area

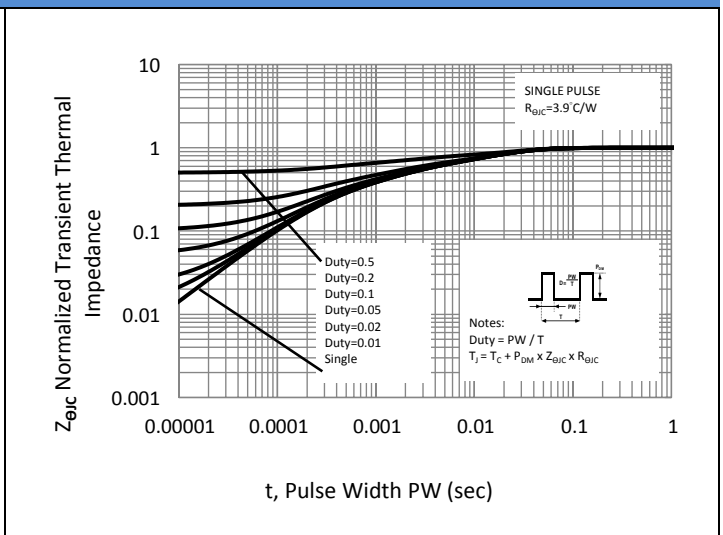


Fig.12 Normalized Transient Thermal Impedance

TYPICAL CHARACTERISTIC CURVES

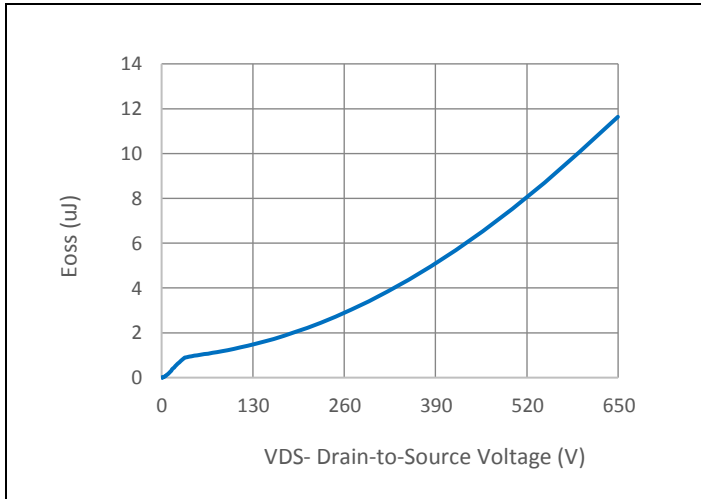
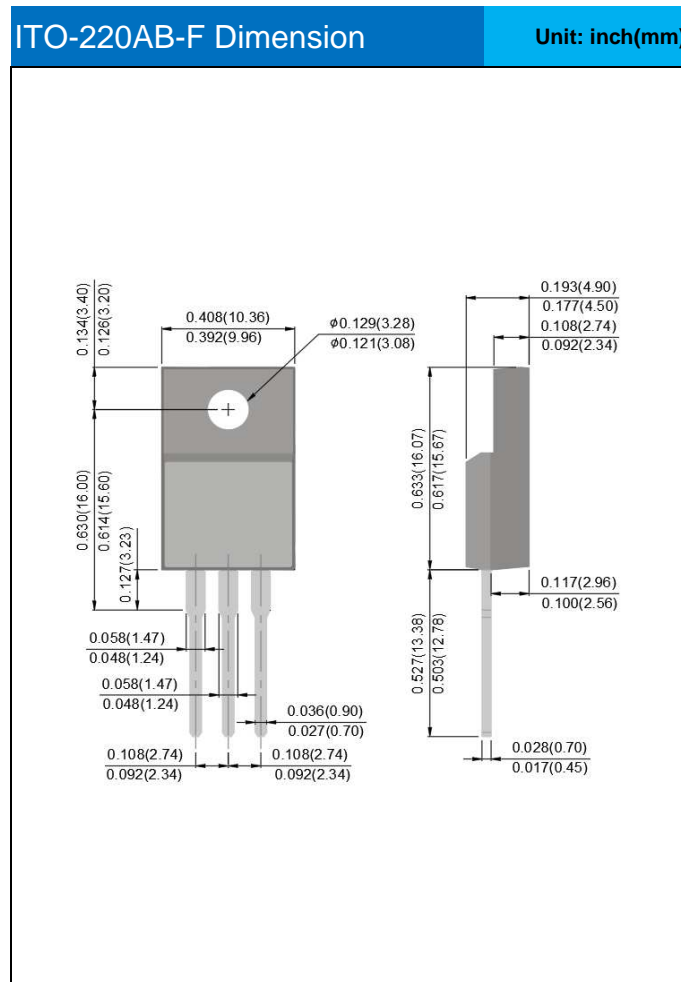


Fig.13 Typ. Coss Stored Energy

Product and Packing Information

Part No.	Package Type	Packing Type	Marking
PJMF210N65EC	ITO-220AB-F	50pcs / Tube	210N65EC

Packaging Information



Marking Diagram

PJ
210N65EC
YWLL x

- Y** = Year Code
- W** = Week Code (A~Z)
- LL** = Lot Code (00~99)
- x** = Production Line Code